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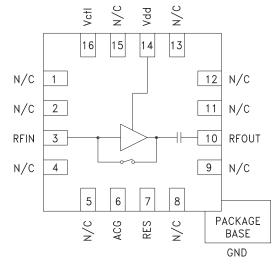
GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

Typical Applications

The HMC668LP3(E) is ideal for:

- Cellular/3G and LTE/WiMAX/4G
- BTS & Infrastructure
- Repeaters and Femtocells
- Tower Mounted Amplifiers
- Test & Measurement Equipment

Functional Diagram



Features

Noise Figure: 0.9 dB Output IP3: +33 dBm Gain: 16 dB Failsafe Operation: Bypass is enabled when LNA is unpowered Single Supply: +3V or +5V 16 Lead 3x3mm QFN Package: 9 mm²

General Description

The HMC668LP3(E) is a versatile, high dynamic range GaAs MMIC Low Noise Amplifier that integrates a low loss LNA bypass mode on the IC. The amplifier is ideal for receivers and LNA modules operating between 0.7 and 1.2 GHz and provides 0.9 dB noise figure, 16 dB of gain and +33 dBm IP3 from a single supply of +5V @ 57mA. Input and output return losses are excellent and no external matching components are required. A single control line is used to switch between LNA mode and a low loss bypass mode. The failsafe topology enables the LNA bypass path, when no DC power is available. The HMC668LP3(E) offers improved noise figure versus the previously released HMC373LP3(E).

Electrical Specifications, $T_A = +25^{\circ}$ C, Rbias = 0 Ohm

	LNA Mode				Bypass Mode		Failsafe Mode						
Parameter	Vdd = +3V		Vdd = +5V		Bypass Mode		Fallsale Mode		Units				
	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	
Frequency Range		0.7 - 1.2		0.7 - 1.2		0.7 - 1.2		0.7 - 1.2		GHz			
Gain	12	15		13	16		-2.5	-1.5		-2.5	-1.5		dB
Gain Variation Over Temperature		0.03			0.016			0.0008			0.0008		dB / °C
Noise Figure		0.85	1.1		0.9	1.1							dB
Input Return Loss		12			13			12			12		dB
Output Return Loss		13			14			13			13		dB
Reverse Isolation		22			23			-			-		dB
Power for 1dB Compression (P1dB) ^[1]		13			13			22			24		dBm
Third Order Intercept (IP3) ^[2]		27			33			26			26		dBm
Supply Current (Idd)		32	40		57	70		0.05			-		mA
Switching Speed (90% -10%)													
LNA Mode to Bypass Mode Bypass Mode to LNA Mode		85			85			200			-		ns ns

[1] P1dB for LNA Mode is referenced to RFOUT while P1dB for Bypass and Failsafe Modes are referenced to RFIN. [2] IP3 for LNA Mode is referenced to RFOUT while IP3 for Bypass and Failsafe Modes are referenced to RFIN.

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HMC668* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

HMC668LP3 Evaluation Board

DOCUMENTATION

Data Sheet

HMC668 Data Sheet

TOOLS AND SIMULATIONS \square

• HMC668 S-Parameter

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: 16L 3x3mm QFN Package (QTR: 11003 REV: 02)
- Package/Assembly Qualification Test Report: LP2, LP2C, LP3, LP3B, LP3C, LP3D, LP3F, LP3G (QTR: 2014-0364)
- Semiconductor Qualification Test Report: PHEMT-D (QTR: 2013-00254)

DESIGN RESOURCES

- HMC668 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC668 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

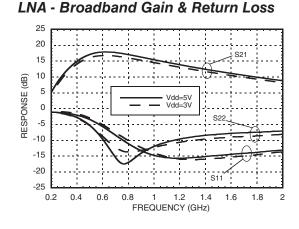
Submit feedback for this data sheet.



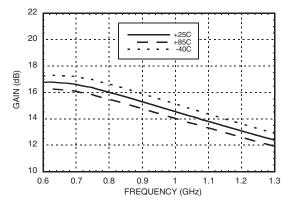
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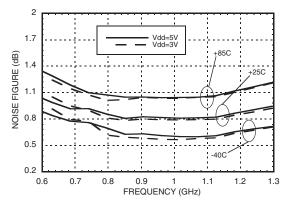
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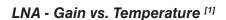


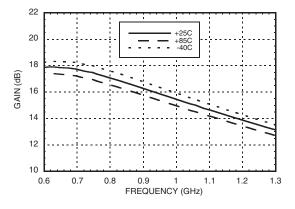
LNA - Gain vs. Temperature [2]

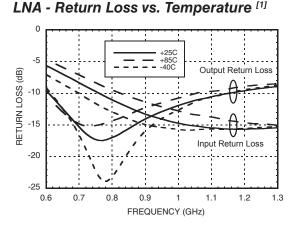


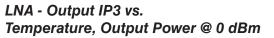
LNA - Noise Figure vs. Temperature [3]

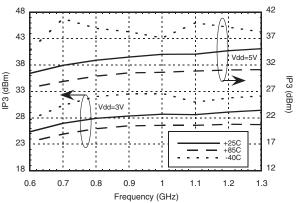












[1] Vdd = 5V [2] Vdd = 3V [3] Measurement reference plane shown on evaluation PCB drawing.

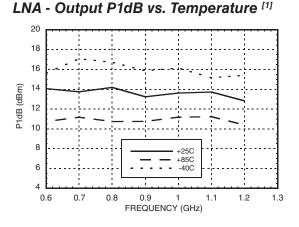
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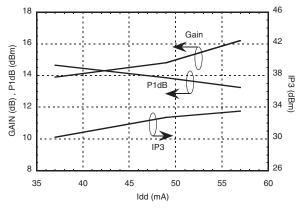
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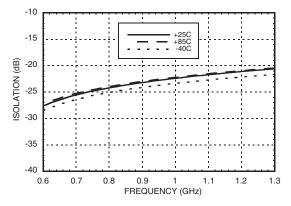
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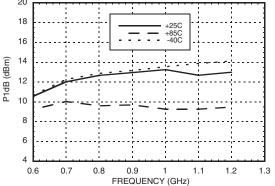
LNA - Gain, P1dB, Output IP3 vs. Current ^[1] @ 900 MHz



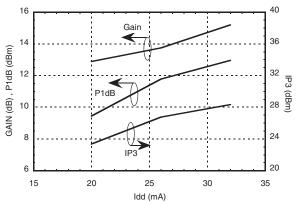
LNA - Reverse Isolation vs. Temperature [1]

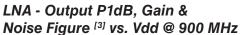


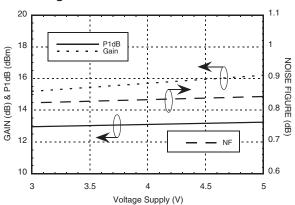
LNA - Output P1dB vs. Temperature ^[2]



LNA - Gain, P1dB, Output IP3 vs. Current ^[2] @ 900 MHz







[1] Vdd = 5V [2] Vdd = 3V [3] Measurement reference plane shown on evaluation PCB drawing.

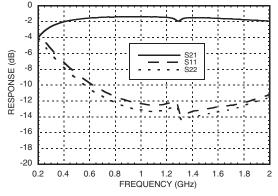
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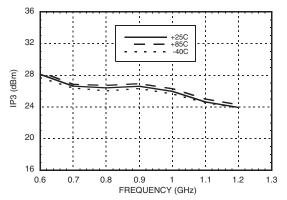
GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

Bypass Mode -Broadband Gain & Return Loss

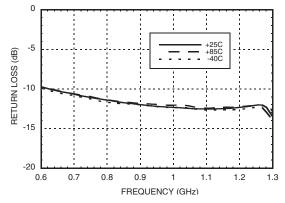


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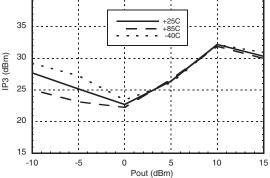
Bypass Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm



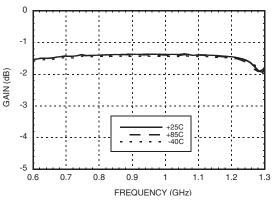
Bypass Mode -Input Return Loss vs. Temperature



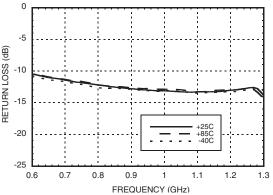
Bypass Mode -Input IP3 vs. Output Power @ 900 MHz



Bypass Mode -Insertion Loss vs. Temperature







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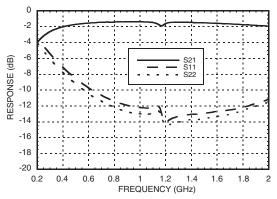
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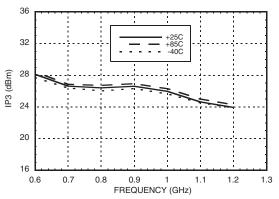


FAILSAFE BYPASS MODE, 700 - 1200 MHz

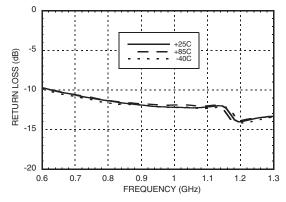
Failsafe Mode -Broadband Gain & Return Loss



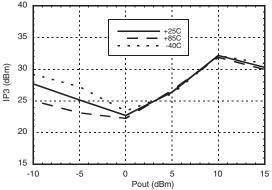
Failsafe Mode - Input IP3 vs. Temperature, Output Power @ 5 dBm



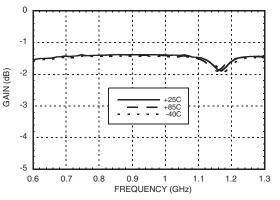
Failsafe Mode -Input Return Loss vs. Temperature



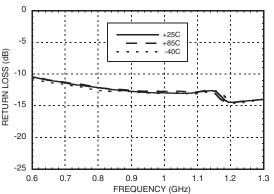
Failsafe Mode -Input IP3 vs. Output Power @ 900 MHz



Failsafe Mode -Insertion Loss vs. Temperature



Failsafe Mode -Output Return Loss vs. Temperature



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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+6 Vdc
Control Voltage (Vctl)	+6 Vdc
RF Input PowerLNA Mode(RFIN)Bypass / Failsafe Mode	+5 dBm +20 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 10.71 mW/°C above 85 °C)	0.70 W
Thermal Resistance (channel to ground paddle)	93.33 °C/W
Storage Temperature	-65 to +150° C
Operating Temperature	-40 to +85° C
ESD Sensitivity (HBM)	Class 1A

v03.0610



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Typical Supply Current vs. Vdd

Rbias Ω	Idd (mA)				
	Vdd= 3V	Vdd= 5V			
0	32	57			
15	26	49			
47	20	37			
180 [1]	10	20			

[1] Recommended maximum Rbias

Truth Table

LNA Mode	VctI = Vdd = 3 to 5V
Bypass Mode	Vctl= 0V, Vdd = 3 to 5V
Failsafe Mode	VctI = Vdd = N/C

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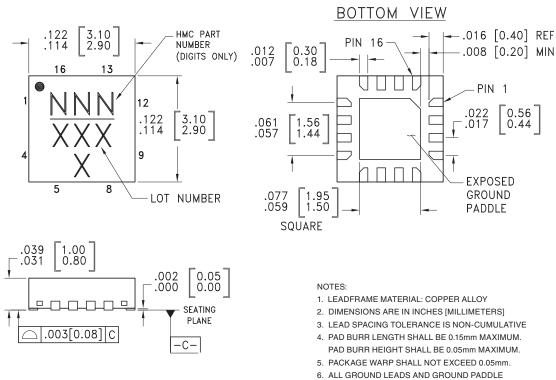


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Outline Drawing



- PACKAGE WARP SHALL NOT EXCEED 0.05m
 ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
 REFER TO HITTITE APPLICATION NOTE FOR
 - SUGGESTED LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC668LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	668 XXXX
HMC668LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>668</u> XXXX

[1] Max peak reflow temperature of 235 $^\circ\text{C}$

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 5, 8, 9, 11, 12, 13, 15	N/C	No connection required. These pins may be connected to RF GND. Performance will not be affected.	
3	RFIN	This pin is DC coupled. Off-chip DC blocking capacitor required.	RFIN O
6	ACG	AC Ground. Attach bypass capacitor per application circuit.	
7	RES	External resistor pin for current control. See table for external resistor value vs. bias current data.	ESD ACG RES
10	RFOUT	This pin is matched to 50 Ohms	
14	Vdd	Power Supply voltage pin. External bypass capacitors required.	Vdd ¢
16	Vctl	Control voltage pin for LNA / Bypass Modes. Setting voltage equal to VDD enables LNA Mode. External Bypass capacitor required.	

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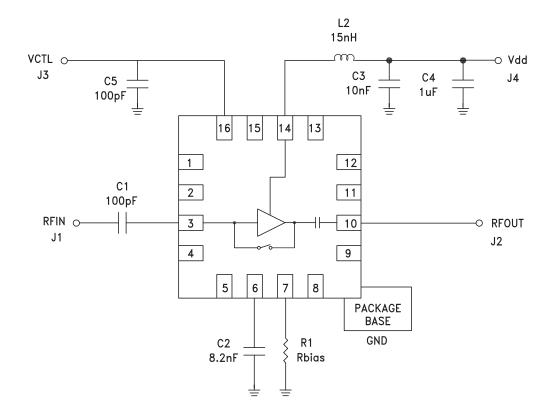


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Application Circuit



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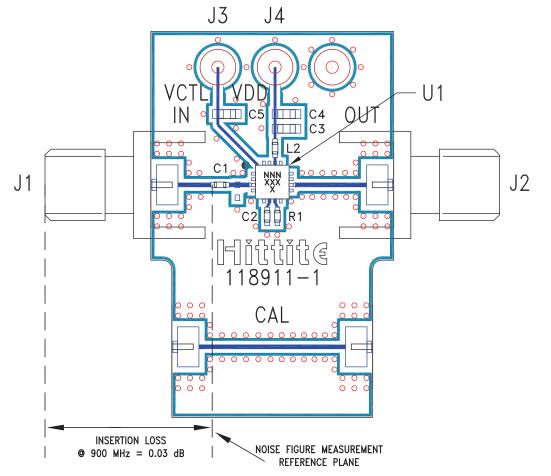


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GaAs PHEMT MMIC LNA w/ FAILSAFE BYPASS MODE, 700 - 1200 MHz

Evaluation PCB



List of Materials for Evaluation PCB 121922 [1]

(
Item	Description	
J1 - J2	PCB Mount SMA Connector	
J3 - J4	DC Pin	
C1	100 pF Capacitor, 0402 Pkg.	
C2	8200 pF Capacitor, 0402 Pkg.	
C3	10 nF Capacitor, 0603 Pkg.	
C4	1 µF Capacitor, 0603 Pkg.	
C5	100 pF Capacitor, 0603 Pkg.	
L2	15 nH Inductor, 0402 Pkg.	
R1	0 Ohm Resistor, 0402 Pkg.	
U1	HMC668LP3(E) Amplifier	
PCB [2]	118911 Evaluation Board	

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

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The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.